

AUTOMOTIVE CURRENT TRANSDUCER HAB 120-V









Introduction

The HABxxx-V Family is for the electronic measurement of DC, AC or pulsed currents in high power automotive applications with galvanic isolation between the primary circuit (high power) and the secondary circuit (electronic circuit).

The HABxxx-V family gives you the choice of having different current measuring ranges in the same housing (from \pm 20 A up to \pm 120 A).

Features

- Open Loop transducer using the Hall effect
- Unipolar + 5 V DC power supply
- Primary current measuring range up to ± 120 A
- Maximum RMS primary current limited by the busbar, the magnetic core or the ASIC temperature T° < + 150°C
- Operating temperature range: 40°C < T° < + 125°C
- Output voltage: full ratiometric (in sensitivity and offset)
- · Compact design.

Advantages

- Excellent accuracy
- Very good linearity
- · Very low thermal offset drift
- Very low thermal sensitivity drift
- Wide frequency bandwidth
- No insertion losses.

Automotive applications

- Battery monitoring
- Starter Generators
- Inverters
- HEV application
- · EV applications.

Principle of HABxxx-V Family

The open loop transducers uses a Hall effect integrated circuit.

The magnetic flux density ${\bf B}$, contributing to the rise of the Hall voltage, is generated by the primary current ${\bf I}_{\rm P}$ to be measured.

The current to be measured I_p is supplied by a current source i.e. battery or generator (Fig. 1).

Within the linear region of the hysteresis cycle, ${\bf B}$ is proportional to:

B
$$(I_p)$$
 = constant (a) x I_p

The Hall voltage is thus expressed by:

$$V_{H} = (R_{H}/d) \times I \times constant (a) \times I_{D}$$

Except for $\mathbf{I}_{\mathrm{p}},$ all terms of this equation are constant. Therefore:

$$V_{H}$$
 = constant (b) x I_{P}

The measurement signal \mathbf{V}_{H} amplified to supply the user output voltage or current.

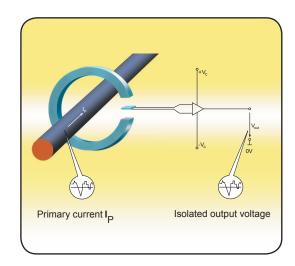
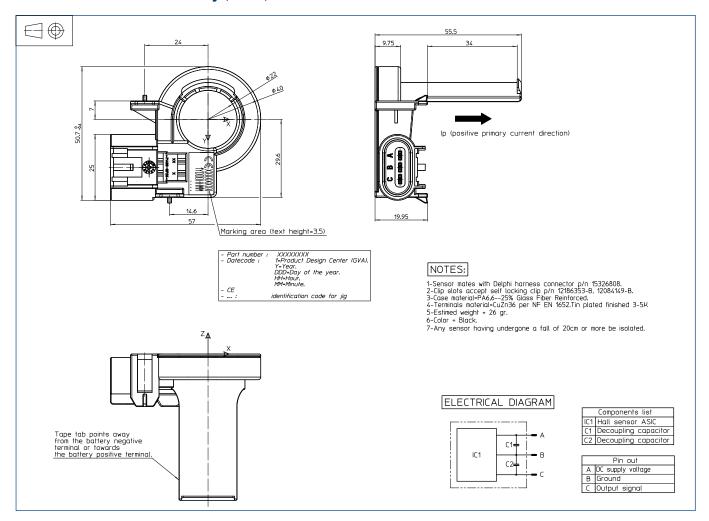


Fig. 1: Principle of the open loop transducer

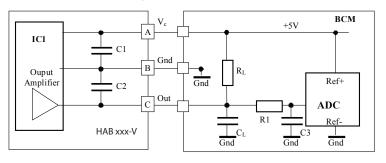


HAB 120-V

Dimensions HABxxx-V family (in mm.)



System artitecture



	HAB120-V components								
IC1	Hall sensor ASIC								
C1	100 nF +/- 20% X7R								
C2	10 nF +/- 20% X7R								

	BCM components							
$R_{\rm L}$	Load Resistor							
C_{L}	Load Capacitor							
R1	Optional High impedance protection							
C3	Optional Filtering Capacitor							



HAB 120-V

Absolute maximum ratings (not operating)

Parameter	Symbol	Unit	Specification			Conditions		
rarameter			Min	Typical	Max	Conditions		
Electrical Data								
Supply continuous over voltage		V			8.5			
Supply over voltage	V _c				14	1 min		
Reverse voltage			-14			1 min @ T _A = 25°C		
Output over voltage (continuous)	V _{out}	V			8.5			
Output over voltage					14	1 min @ T _A = 25°C		
Output current (continuous)	out	mA	-10		10			
Output short-circuit duration	T _c	min			2			
Rms voltage isolation test	V _d	kV			2	IEC 60664-1		
Electrostatic discharge voltage	V _{ESD}	kV			2	IEC 61000-4-2		
Ambiant storage temperature T _s		°C	- 40		125			

Operating characteristics

Parameter	Symbol	Unit	Specification			Conditions
Farameter			Min	Typical	Max	Conditions
			Electri	cal Data		
Primary current	I _P	Α	- 120		120	
Calibration current	CAL		- 60		60	@ T _A = 25°C
Supply voltage	V _c	V	4.5	5.00	5.5	
Output voltage 1)	V _{out}	V	V _{OUT} = V	$V_{OUT} = V_{C}/5 \times (2.5 + 0.017 \times I_{P})$		@ V _c
Sensitivity 1)	G	mV/A		17.00		@ V _C = 5 V
Current consumption		mΛ		7	10	@ $V_{\rm C}$ = 5 V, - 40°C < $T_{\rm A}$ < 125 °C
Power up inrush current 2)	I _c	mA			15	@ V _c < 3.5 V
Load resistance	R _∟	kΩ	10			
Ouput internal resistance	R _{OUT}	Ω			10	
Capacitive loading	C _L	nF	1		100	
Ambiant operating temperature	T _A	°C	- 40		125	
Output drift versus power supply	drift versus power supply % 0.5					
Frequency bandwidth 2)	BW	Hz		80		@ -3 dB
Output clamping voltage min	V	V	0.2	0.25	0.3	@ V _C = 5 V
Output clamping voltage max	V _{sz}	V	4.7	4.75	4.8	@ V _C = 5 V
Output voltage noise peak-peak	V _{no p-p}	mV			10	
Resolution		mV		2.5		@ V _c = 5 V
Power up time		ms	25 110		110	
Setting time after over load	etting time after over load ms 25		25			

Notes: 1) The output voltage \mathbf{V}_{OUT} is fully ratiometric. The offset and sensitivity are dependent on the supply voltage \mathbf{V}_{C} relative to the following formula:

$$I_{P} = \left(V_{\text{out}} - \frac{V_{c}}{2}\right) \times \frac{1}{G} \times \frac{5}{V_{c}} \quad \text{with G in (V/A)}$$

²⁾ During the power up phase.



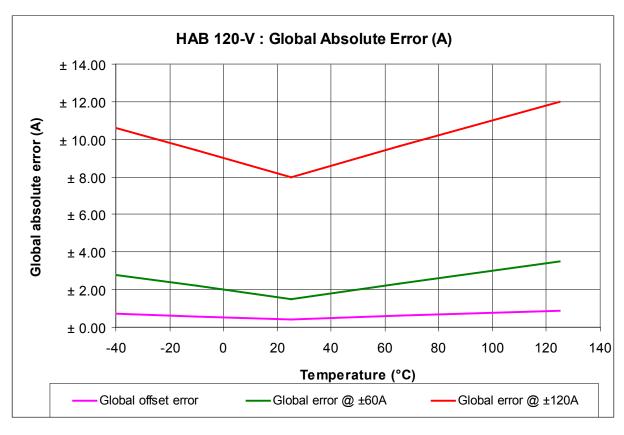
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Accuracy

Parameter	Symbol	Unit	Specification			Conditions		
Faranietei	Symbol		Min	Тур	Max	Conditions		
Electrical Data								
Electrical offset current	I _{OE}			± 0.20		@ T _A = 25°C, @ V _C = 5 V		
Magnetic offset current	I _{OM}			± 0.05		@ $T_A = 25^{\circ}C$, @ $V_C = 5$ V, after $\pm I_P$		
		A	- 0.4		0.4	0 T _A = 25°C, 0 V _C = 5 V		
Global offset current	I _o		- 0.6		0.6	$@V_{C} = 5 \text{ V}, -10^{\circ}\text{C} < T_{A} < 65^{\circ}\text{C}$		
			- 0.9		0.9	@ V _C = 5 V, -40°C < T _A < 125°C		
		%		± 0.3		@ T _A = 25°C , I _P = ± 60 A		
Sensitivity error	ε _G			±1.0		@ - 10°C < T° < 65°C, I _P = ± 60A		
				± 2.0		@ - 40°C < T° < 125°C, I _p = ± 60A		
Linearity error up to 60A		%		± 0.2				
Linearity error up to 80A	ε _L			± 1.0		of full range		
Linearity error up to 120A				± 2.5				

Global Absolute Error (A)

	Global Absolute Error (A)								
Temperature	-40	-10	25	65	125				
Global Offset Error	± 0.73	± 0.58	± 0.40	± 0.60	± 0.90				
Global Error @±60A	± 2.80	± 2.20	± 1.50	± 2.30	± 3.50				
Global Error @±120A	± 10.60	± 9.40	± 8.00	± 9.60	± 12.00				





HAB 120-V PERFORMANCES PARAMETERS DEFINITIONS

Output noise voltage:

The output voltage noise is the result of the noise floor of the Hall elements and the linear I_c amplifier gain.

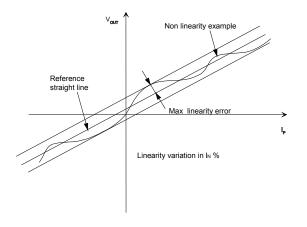
Magnetic offset:

The magnetic offset is the consequence of an over-current on the primary side. It's defined after an excursion of $I_{\rm P\,max}$.

Linearity:

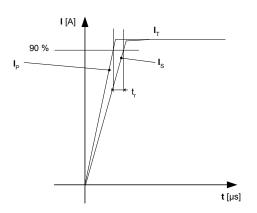
The maximum positive or negative discrepancy with a reference straight line \mathbf{V}_{OUT} = f (\mathbf{I}_{p}).

Unit: linearity (%) expressed with full scale of I_{P max}.



Response time (delay time) t.:

The time between the primary current signal and the output signal reach at 90 % of its final value



Typical:

Theorical value or usual accuracy recorded during the production.

Sensitivity:

The Transducer's sensitivity **G** is the slope of the straight line $V_{out} = f(I_p)$, it must establish the relation:

 $V_{out}(I_{p}) = V_{c}/5 (G \times I_{p} + 2.5) (*)$

(*) For all symetrics transducers.

Offset with temperature:

The error of the offset in the operating temperature is the variation of the offset in the temperature considered with the initial offset at 25°C.

The offset variation \mathbf{I}_{OT} is a maximum variation the offset in the temperature range:

 $I_{OT} = I_{OE} \max - I_{OE} \min$

The Offset drift \mathbf{TCI}_{OEAV} is the \mathbf{I}_{OT} value divided by the temperature range.

Sensitivity with temperature:

The error of the sensitivity in the operating temperature is the relative variation of sensitivity with the temperature considered with the initial offset at 25°C.

The sensitivity variation \mathbf{G}_{T} is the maximum variation (in ppm or %) of the sensitivity in the temperature range:

 $\mathbf{G}_{\scriptscriptstyle T}$ = (Sensitivity max - Sensitivity min) / Sensitivity at 25°C.

The sensitivity drift \mathbf{TCG}_{AV} is the \mathbf{G}_{T} value divided by the temperature range.

Offset voltage @ Ip = 0 A:

Is the output voltage when the primary current is null. The ideal value of \mathbf{V}_{O} is $\mathbf{V}_{\text{C}}/2$ at $\mathbf{V}_{\text{C}}=5$ V. So, the difference of \mathbf{V}_{O} - $\mathbf{V}_{\text{C}}/2$ is called the total offset voltage error. This offset error can be attributed to the electrical offset (due to the resolution of the ASIC quiescent voltage trimming), the magnetic offset, the thermal drift and the thermal hysteresis.